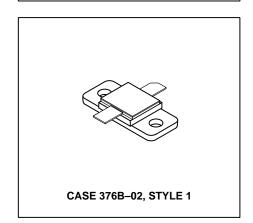
# The RF Line Microwave Pulse Power Transistor

... designed for 1025-1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode-S transmitters.

- Guaranteed Performance @ 1090 MHz
   Output Power = 150 Watts Peak
   Gain = 9.5 dB Min, 10.0 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Package
- · Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- · Internal Input and Output Matching
- Characterized with 10 μs, 10% Duty Cycle Pulses
- Recommended Driver for a Pair of MRF10500 Transistors

## **MRF10150**

150 W (PEAK) 1025-1150 MHz MICROWAVE POWER TRANSISTOR NPN SILICON



#### **MAXIMUM RATINGS**

| Rating   | Symb             | ool Value   | Unit          |
|--|------------------|-------------|---------------|
| Collector–Emitter Voltage  | VCE              | S 65        | Vdc           |
| Collector–Base Voltage   | V <sub>CB</sub>  | O 65        | Vdc           |
| Emitter-Base Voltage   | VEB              | O 3.5       | Vdc           |
| Collector Current — Peak (1)   | lC               | 14          | Adc           |
| Total Device Dissipation @ T <sub>C</sub> = 25°C (1), (2)<br>Derate above 25°C | PD               | 700<br>4.0  | Watts<br>W/°C |
| Storage Temperature Range  | T <sub>stç</sub> | -65 to +200 | °C            |
| Junction Temperature   | TJ               | 200         | °C            |

#### THERMAL CHARACTERISTICS

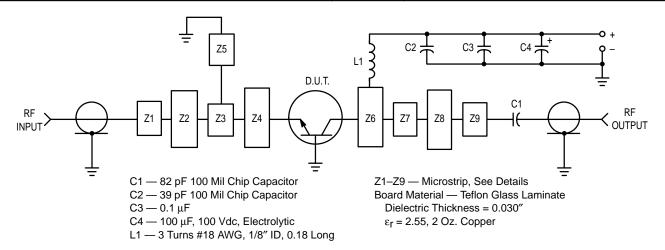
| Characteristic                           | Symbol          | Max  | Unit |
|--|-----------------|------|------|
| Thermal Resistance, Junction to Case (3) | $R_{\theta JC}$ | 0.25 | °C/W |

### NOTES:

- 1. Under pulse RF operating conditions.
- 2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
- 3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ<sub>JC</sub> value measured @ 10 μs, 10%.)



| Characteristic  | Complete        | Min                            | T   | Mari | 11   |  |
|---|-----------------|--------------------------------|-----|------|------|--|
| Characteristic  | Symbol          | Min                            | Тур | Max  | Unit |  |
| OFF CHARACTERISTICS   |                 |                                |     |      |      |  |
| Collector–Emitter Breakdown Voltage ( $I_C = 60 \text{ mAdc}$ , $V_{BE} = 0$ )                                      | V(BR)CES        | 65                             | _   | _    | Vdc  |  |
| Collector–Base Breakdown Voltage (I <sub>C</sub> = 60 mAdc, I <sub>E</sub> = 0)                                     | V(BR)CBO        | 65                             | _   | _    | Vdc  |  |
| Emitter–Base Breakdown Voltage ( $I_E = 10 \text{ mAdc}, I_C = 0$ )   | V(BR)EBO        | 3.5                            | _   | _    | Vdc  |  |
| Collector Cutoff Current (V <sub>CB</sub> = 36 Vdc, I <sub>E</sub> = 0)   | ICBO            | _                              | _   | 25   | mAdc |  |
| ON CHARACTERISTICS  | •               |                                |     |      |      |  |
| DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 5.0 Vdc)   | hFE             | 20                             | _   | _    | _    |  |
| FUNCTIONAL TESTS  | •               |                                |     |      |      |  |
| Common–Base Amplifier Power Gain<br>(V <sub>CC</sub> = 50 Vdc, P <sub>Out</sub> = 150 W Peak, f = 1090 MHz)         | G <sub>PB</sub> | 9.5                            | 10  | _    | dB   |  |
| Collector Efficiency<br>(V <sub>CC</sub> = 50 Vdc, P <sub>Out</sub> = 150 W Peak, f = 1090 MHz)                     | η               | 40                             | _   | _    | %    |  |
| Load Mismatch (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 150 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles) | Ψ               | No Degradation in Output Power |     |      |      |  |



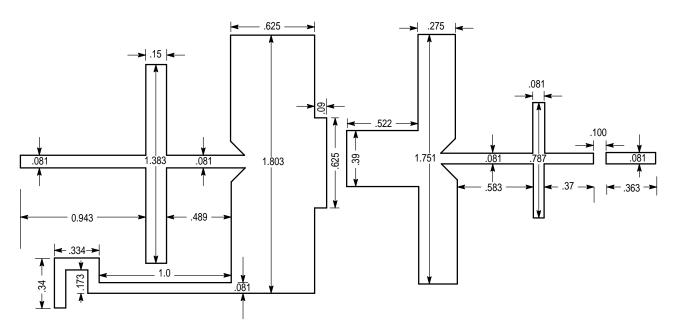


Figure 1. Test Circuit

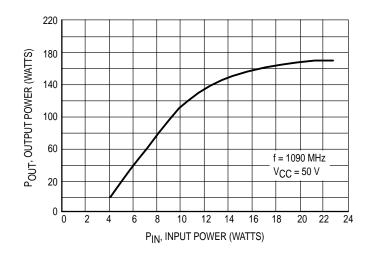
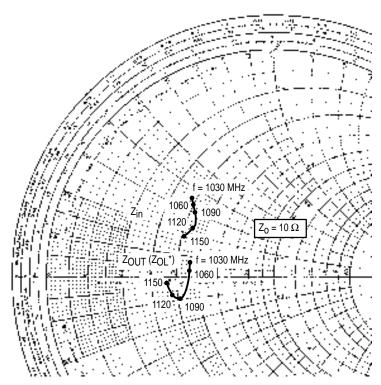


Figure 2. Output Power versus Input Power



P<sub>OUT</sub> = 150 W Pk V<sub>CC</sub> = 50 V

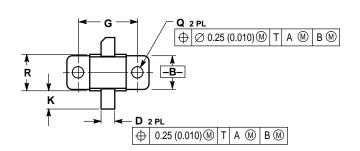
| f<br>MHz | Z <sub>in</sub><br>OHMS | Z <sub>OL*</sub> (Z <sub>OUT</sub> )<br>OHMS |
|----------|-------------------------|--|
| 1030     | 3.8 + j3.5              | 4.6 + j0.7                                   |
| 1060     | 4.0 + j3.3              | 4.6 + j0.3                                   |
| 1090     | 4.2 + j3.0              | 4.1 – j1.0                                   |
| 1120     | 4.4 + j2.3              | 3.8 – j0.8                                   |
| 1150     | 4.1 + j1.8              | 3.6 – j0.3                                   |

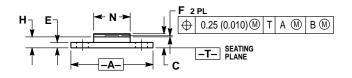
 $\mathbf{Z}_{OL}{}^{\star}$  is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

MRF10150 3 MOTOROLA RF DEVICE DATA

#### PACKAGE DIMENSIONS





CASE 376B-02 **ISSUE B** 

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

|     | INCHES    |       | MILLIN    | IETERS |  |
|-----|-----------|-------|-----------|--------|--|
| DIM | MIN       | MAX   | MIN       | MAX    |  |
| Α   | 0.890     | 0.910 | 22.61     | 23.11  |  |
| В   | 0.370     | 0.400 | 9.40      | 10.16  |  |
| С   | 0.145     | 0.160 | 3.69      | 4.06   |  |
| D   | 0.140     | 0.160 | 3.56      | 4.06   |  |
| Е   | 0.055     | 0.065 | 1.40      | 1.65   |  |
| F   | 0.003     | 0.006 | 0.08      | 0.15   |  |
| G   | 0.650 BSC |       | 16.51 BSC |        |  |
| Н   | 0.110     | 0.130 | 2.80      | 3.30   |  |
| K   | 0.180     | 0.220 | 4.57      | 5.59   |  |
| N   | 0.390     | 0.410 | 9.91      | 10.41  |  |
| Q   | 0.115     | 0.135 | 2.93      | 3.42   |  |
| R   | 0.390     | 0.140 | 9 91      | 10.41  |  |

PIN 1. COLLECTOR 2. EMITTER

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